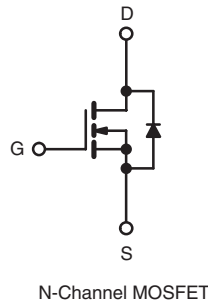
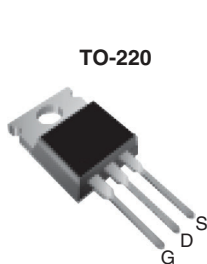


## Power MOSFET

| PRODUCT SUMMARY           |                              |
|---------------------------|------------------------------|
| $V_{DS}$ (V)              | 60                           |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 10\text{ V}$ 0.050 |
| $Q_g$ (Max.) (nC)         | 46                           |
| $Q_{gs}$ (nC)             | 11                           |
| $Q_{gd}$ (nC)             | 22                           |
| Configuration             | Single                       |



### FEATURES

- Dynamic  $dV/dt$  Rating
- 175 °C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available



Available  
**RoHS\***  
COMPLIANT

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.

| ORDERING INFORMATION |            |
|----------------------|------------|
| Package              | TO-220     |
| Lead (Pb)-free       | IRFZ34PbF  |
|                      | SiHFZ34-E3 |
| SnPb                 | IRFZ34     |
|                      | SiHFZ34    |

| ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted |                                  |                |                                   |          |
|--|----------------------------------|----------------|-----------------------------------|----------|
| PARAMETER  |                                  | SYMBOL         | LIMIT                             | UNIT     |
| Drain-Source Voltage   |                                  | $V_{DS}$       | 60                                | V        |
| Gate-Source Voltage  |                                  | $V_{GS}$       | $\pm 20$                          |          |
| Continuous Drain Current   | $V_{GS}$ at 10 V                 | $I_D$          | $T_C = 25\text{ }^\circ\text{C}$  | A        |
|  |                                  |                | $T_C = 100\text{ }^\circ\text{C}$ |          |
| Pulsed Drain Current <sup>a</sup>  |                                  | $I_{DM}$       | 120                               |          |
| Linear Derating Factor   |                                  |                | 0.59                              | W/°C     |
| Single Pulse Avalanche Energy <sup>b</sup>   |                                  | $E_{AS}$       | 200                               | mJ       |
| Maximum Power Dissipation  | $T_C = 25\text{ }^\circ\text{C}$ | $P_D$          | 88                                | W        |
| Peak Diode Recovery $dV/dt^c$  |                                  | $dV/dt$        | 4.5                               | V/ns     |
| Operating Junction and Storage Temperature Range                                   |                                  | $T_J, T_{stg}$ | - 55 to + 175                     | °C       |
| Soldering Recommendations (Peak Temperature)                                       | for 10 s                         |                | 300 <sup>d</sup>                  |          |
| Mounting Torque  | 6-32 or M3 screw                 |                | 10                                | lbf · in |
|  |                                  |                | 1.1                               | N · m    |

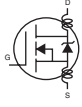

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 259\text{ }\mu\text{H}$ ,  $R_G = 25\text{ }\Omega$ ,  $I_{AS} = 30\text{ A}$  (see fig. 12).
- $I_{SD} \leq 30\text{ A}$ ,  $dI/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

| THERMAL RESISTANCE RATINGS          |            |      |      |      |
|-------------------------------------|------------|------|------|------|
| PARAMETER                           | SYMBOL     | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient         | $R_{thJA}$ | -    | 62   | °C/W |
| Case-to-Sink, Flat, Greased Surface | $R_{thCS}$ | 0.50 | -    |      |
| Maximum Junction-to-Case (Drain)    | $R_{thJC}$ | -    | 1.7  |      |

**SPECIFICATIONS**  $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted

| PARAMETER                                      | SYMBOL              | TEST CONDITIONS   | MIN. | TYP.  | MAX.      | UNIT          |
|--|---------------------|---|------|-------|-----------|---------------|
| <b>Static</b>                                  |                     |   |      |       |           |               |
| Drain-Source Breakdown Voltage                 | $V_{DS}$            | $V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$  | 60   | -     | -         | V             |
| $V_{DS}$ Temperature Coefficient               | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$   | -    | 0.065 | -         | V/°C          |
| Gate-Source Threshold Voltage                  | $V_{GS(th)}$        | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$  | 2.0  | -     | 4.0       | V             |
| Gate-Source Leakage                            | $I_{GSS}$           | $V_{GS} = \pm 20\text{ V}$  | -    | -     | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current                | $I_{DSS}$           | $V_{DS} = 60\text{ V}$ , $V_{GS} = 0\text{ V}$  | -    | -     | 25        | $\mu\text{A}$ |
|  |                     | $V_{DS} = 48\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$  | -    | -     | 250       |               |
| Drain-Source On-State Resistance               | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}$   $I_D = 18\text{ A}^b$  | -    | -     | 0.050     | $\Omega$      |
| Forward Transconductance                       | $g_{fs}$            | $V_{DS} = 25\text{ V}$ , $I_D = 18\text{ A}$  | 9.3  | -     | -         | S             |
| <b>Dynamic</b>                                 |                     |   |      |       |           |               |
| Input Capacitance                              | $C_{iss}$           | $V_{GS} = 0\text{ V}$ ,<br>$V_{DS} = 25\text{ V}$ ,<br>$f = 1.0\text{ MHz}$ , see fig. 5  | -    | 1200  | -         | pF            |
| Output Capacitance                             | $C_{oss}$           |   | -    | 600   | -         |               |
| Reverse Transfer Capacitance                   | $C_{rss}$           |   | -    | 100   | -         |               |
| Total Gate Charge                              | $Q_g$               | $V_{GS} = 10\text{ V}$   $I_D = 30\text{ A}$ , $V_{DS} = 48\text{ V}$ ,<br>see fig. 6 and 13 <sup>b</sup>   | -    | -     | 46        | nC            |
| Gate-Source Charge                             | $Q_{gs}$            |   | -    | -     | 11        |               |
| Gate-Drain Charge                              | $Q_{gd}$            |   | -    | -     | 22        |               |
| Turn-On Delay Time                             | $t_{d(on)}$         | $V_{DD} = 30\text{ V}$ , $I_D = 30\text{ A}$ ,<br>$R_G = 12\text{ }\Omega$ , $R_D = 1.0\text{ }\Omega$ , see fig. 10 <sup>b</sup>                               | -    | 13    | -         | ns            |
| Rise Time                                      | $t_r$               |   | -    | 100   | -         |               |
| Turn-Off Delay Time                            | $t_{d(off)}$        |   | -    | 29    | -         |               |
| Fall Time                                      | $t_f$               |   | -    | 52    | -         |               |
| Internal Drain Inductance                      | $L_D$               | Between lead,<br>6 mm (0.25") from<br>package and center of<br>die contact  | -    | 4.5   | -         | nH            |
| Internal Source Inductance                     | $L_S$               |   | -    | 7.5   | -         |               |
| <b>Drain-Source Body Diode Characteristics</b> |                     |   |      |       |           |               |
| Continuous Source-Drain Diode Current          | $I_S$               | MOSFET symbol<br>showing the<br>integral reverse<br>p - n junction diode    | -    | -     | 30        | A             |
| Pulsed Diode Forward Current <sup>a</sup>      | $I_{SM}$            |   | -    | -     | 120       |               |
| Body Diode Voltage                             | $V_{SD}$            | $T_J = 25\text{ }^\circ\text{C}$ , $I_S = 30\text{ A}$ , $V_{GS} = 0\text{ V}^b$  | -    | -     | 1.6       | V             |
| Body Diode Reverse Recovery Time               | $t_{rr}$            | $T_J = 25\text{ }^\circ\text{C}$ , $I_F = 30\text{ A}$ , $dI/dt = 100\text{ A}/\mu\text{s}$   | -    | 120   | 230       | ns            |
| Body Diode Reverse Recovery Charge             | $Q_{rr}$            |   | -    | 0.7   | 1.4       | nC            |
| Forward Turn-On Time                           | $t_{on}$            | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )   |      |       |           |               |

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

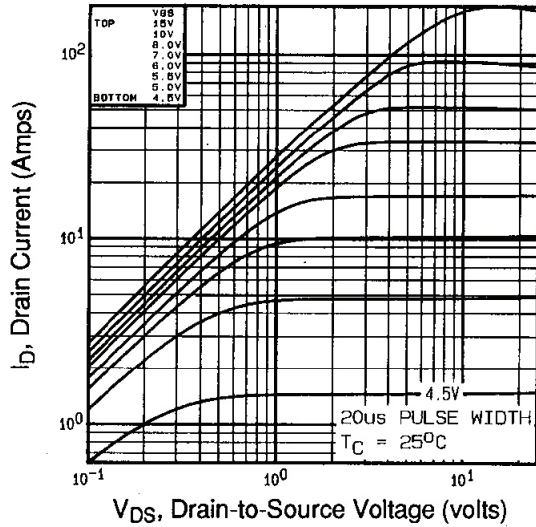


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$

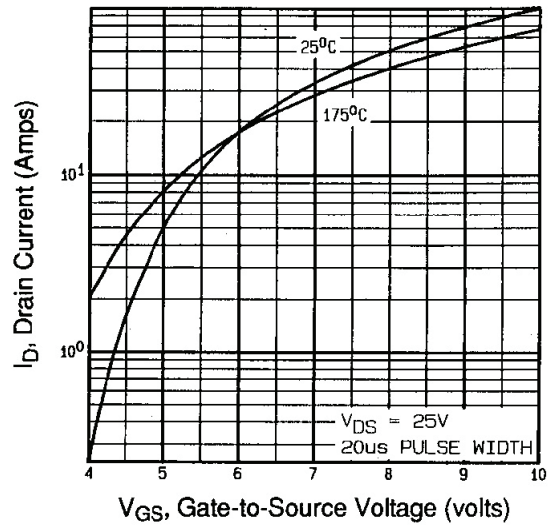


Fig. 3 - Typical Transfer Characteristics

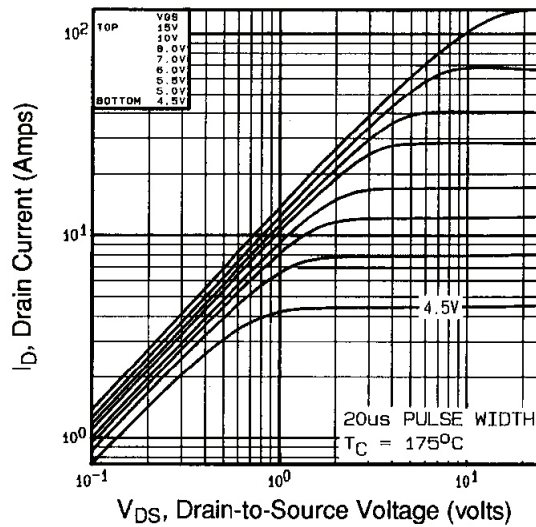


Fig. 2 - Typical Output Characteristics,  $T_C = 175\text{ }^\circ\text{C}$

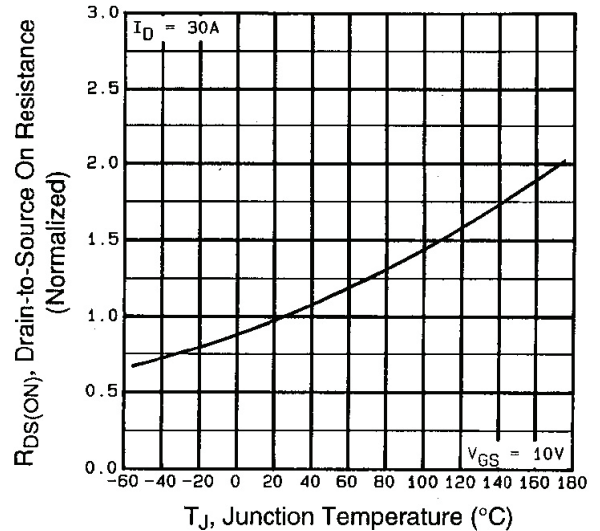


Fig. 4 - Normalized On-Resistance vs. Temperature

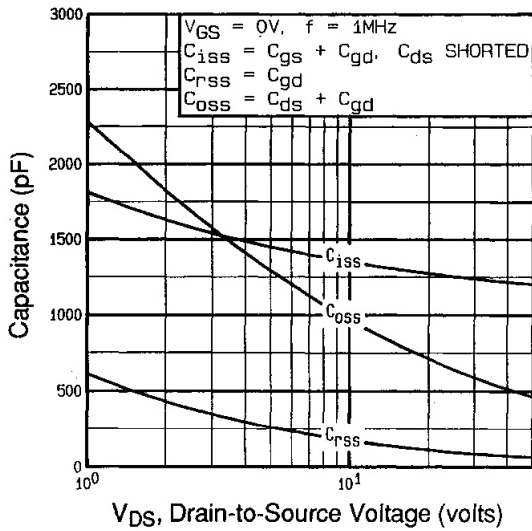


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

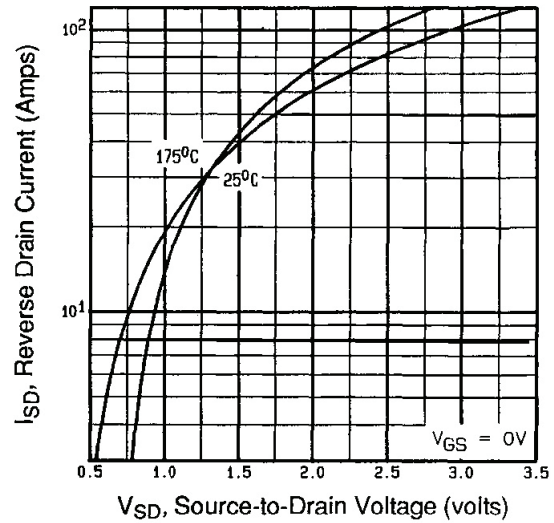


Fig. 7 - Typical Source-Drain Diode Forward Voltage

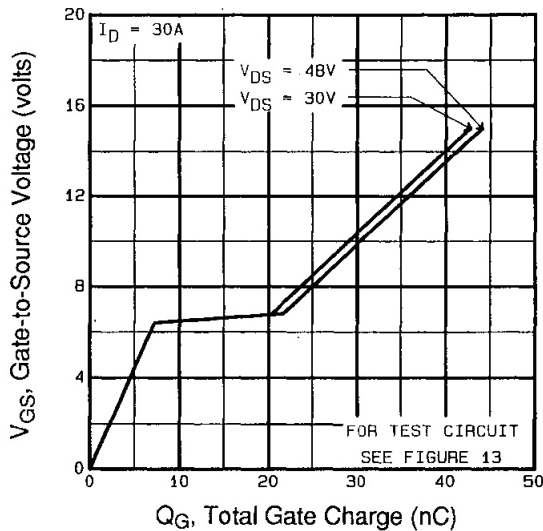


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

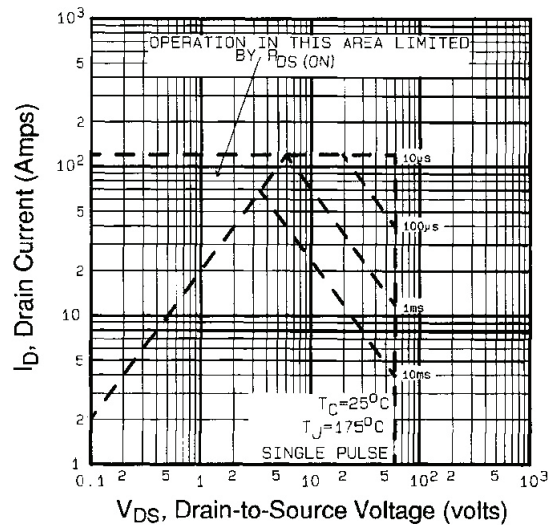


Fig. 8 - Maximum Safe Operating Area

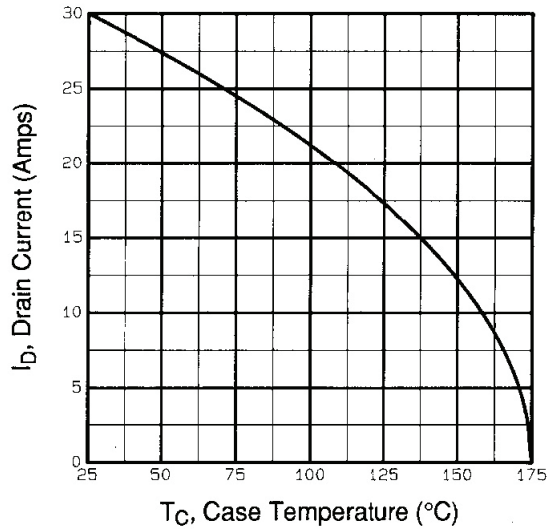


Fig. 9 - Maximum Drain Current vs. Case Temperature

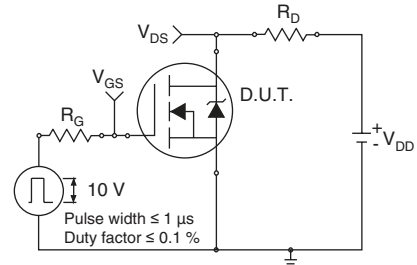


Fig. 10a - Switching Time Test Circuit

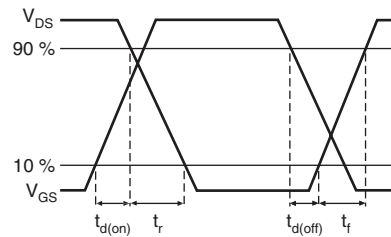


Fig. 10b - Switching Time Waveforms

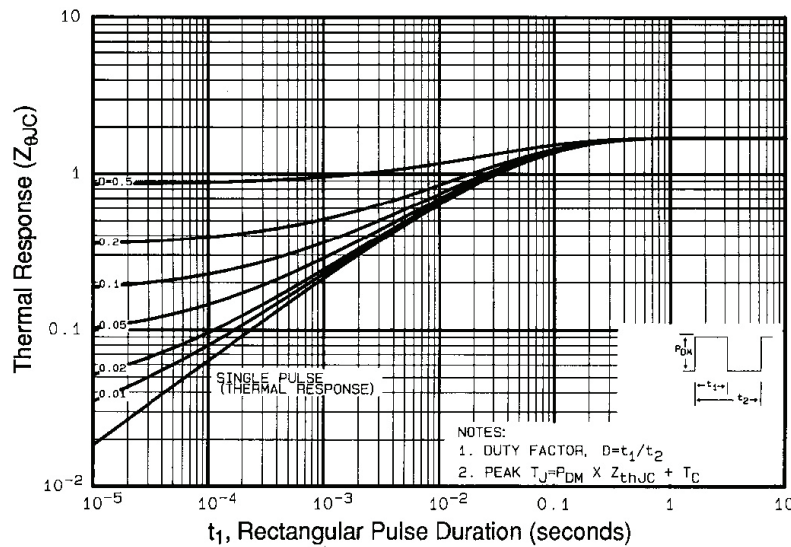


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

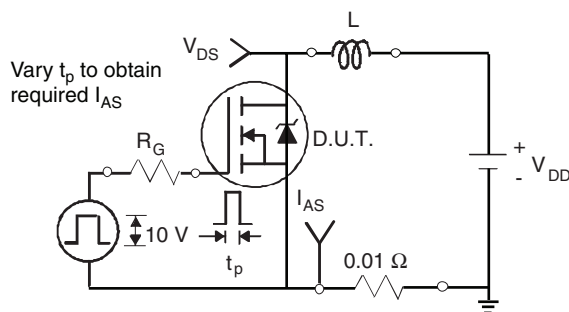


Fig. 12a - Unclamped Inductive Test Circuit

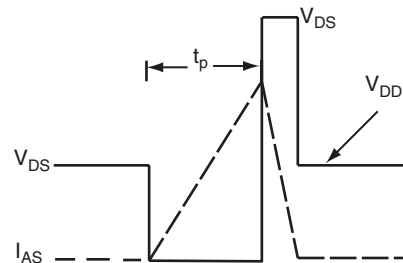


Fig. 12b - Unclamped Inductive Waveforms

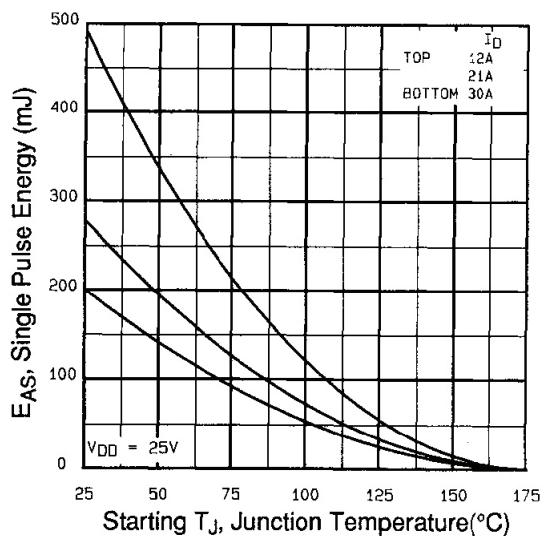


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

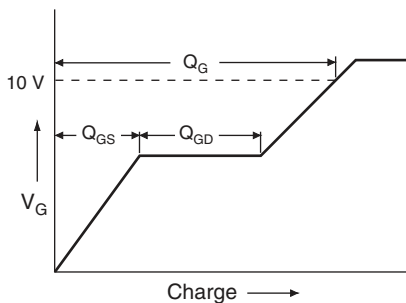


Fig. 13a - Basic Gate Charge Waveform

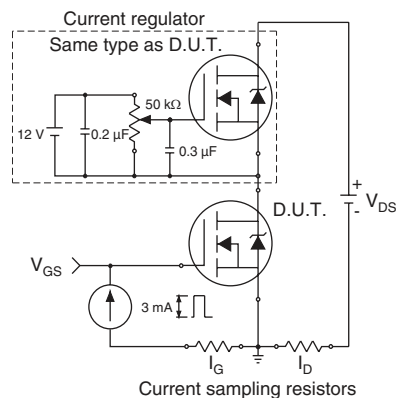
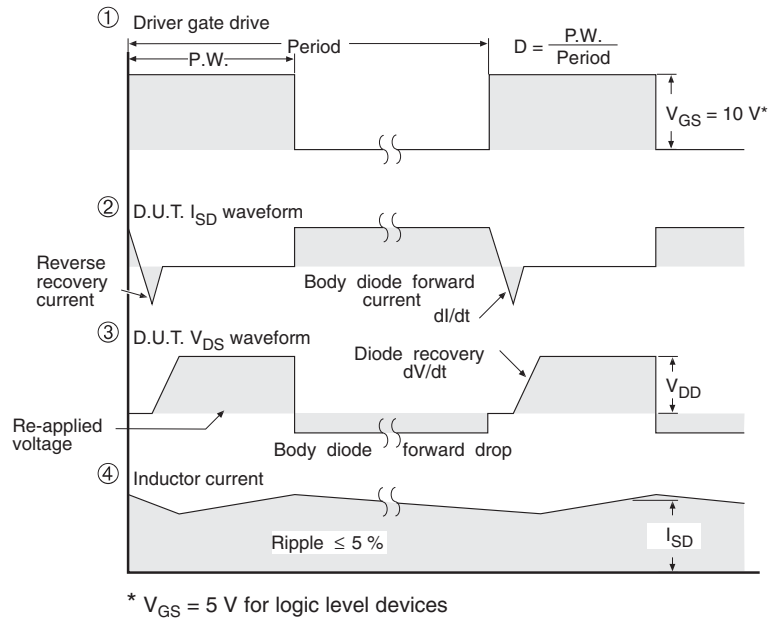
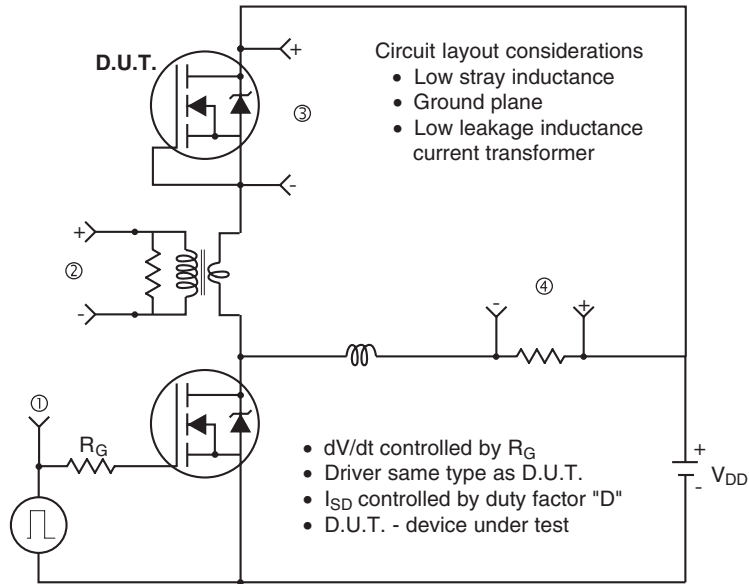


Fig. 13b - Gate Charge Test

**Peak Diode Recovery dV/dt Test Circuit**

**Fig. 14 - For N-Channel**

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